L Number	Hits	Search Text	DB	Time stamp
1	1	"10/080,539"	USPAT;	2004/06/10 15:59
			US-PGPUB	1201,00,10 10.05
2	100	kagoshima-akira.in. yamamoto-hideyuki.in.	USPAT;	2004/06/10 16:00
		torii-yoshimi.in.	US-PGPUB	3000,00,10
3	31	(kagoshima-akira.in. yamamoto-hideyuki.in.	USPAT;	2004/06/10 16:05
		torii-yoshimi.in.) and (control\$4 with	US-PGPUB	
		etch\$3) and ash\$3		
4	0	(204/298.35.ccls. 204/298.25.ccls.	USPAT;	2004/06/10 16:07
		204/298.32.ccls.) and (etch\$3 same ash\$3	US-PGPUB	]
		same control\$4 same (transfer\$4		
1		transport\$4) same order)	İ	
5	46	( )	USPAT;	2004/06/10 16:07
		204/298.32.ccls.) and (control\$4 same	US-PGPUB	
		(transfer\$4 transport\$4) same order)		
6	3	(=	USPAT;	2004/06/10 16:08
		204/298.32.ccls.) and (( order near	US-PGPUB	
	8	control\$4) same (transfer\$4 transport\$4) )		
-	8	118/719.ccls. and (chamber with pressure	USPAT;	2004/06/10 11:26
	1	with higher with prevent) ("20010040145").PN.	US-PGPUB	2002/00/06 40 40
]		( 2001004014J ).PN.	USPAT;	2003/02/26 10:13
_	196	156/345.24	US-PGPUB USPAT;	2003/08/22 16:30
	1,0	100,010121	USPAT; US-PGPUB	2003/08/22 16:30
_	600	((156/345.24) or (156/345.51) or	USPAT;	2003/08/22 16:31
	300	(156/345.52) or (156/345.53)).CCLS.	US-PGPUB	2003/08/22 16:31
l – i	177	(((156/345.24) or (156/345.51) or	USPAT;	2004/06/09 19:43
		(156/345.52) or (156/345.53)).CCLS.) and	US-PGPUB	2001,00,03 13.43
		(control\$3 with (substrate wafer target)		
	i	with temperature)		<b>†</b>
-	4	((((156/345.24) or (156/345.51) or	USPAT;	2003/08/22 17:14
		(156/345.52) or (156/345.53)).CCLS.) and	US-PGPUB	
		(control\$3 with (substrate wafer target)		
		with temperature)) and ((high with		
		densit\$3) same (low with ion\$6))		1
-	728	(156/345.\$.CCLS.) and (control\$3 with	USPAT;	2004/06/09 19:44
	140	(substrate wafer target) with temperature)	US-PGPUB	
-	142	(156/345.\$.CCLS.) and (control\$3 with	USPAT;	2004/06/09 19:44
		(substrate wafer target) with temperature	US-PGPUB	
_	166	with etch\$3) (156/345.\$.CCLS.) and (control\$4 with	TIODE TO	2004/06/00 40 46
	100	(substrate wafer target) with temperature	USPAT; US-PGPUB	2004/06/09 19:46
		with etch\$3)	US-PGPUB	
-	131	(156/345.\$.CCLS.) and (control\$4 with	USPAT;	2004/06/09 19:46
1	131	(substrate wafer target) with temperature	US-PGPUB	2004/06/09 19:46
		with during with (process\$3 treatm\$3))	70 1G10D	
-	2	(156/345.\$.CCLS.) and (control\$4 with	USPAT;	2004/06/09 19:47
	_	(substrate wafer target) with temperature	US-PGPUB	== 0.1, 0.0, 0.5 1.5, 4,
		with during with (process\$3 treatm\$3) with		
		damag\$3)		
-	39	(control\$4 with (substrate wafer target)	USPAT;	2004/06/09 19:56
		with temperature with during with	US-PGPUB	
	_	(process\$3 treatm\$3) with damag\$3)		
-	0	(118/719.ccls. 156/345.31.ccls.	USPAT;	2004/06/09 20:00
		156/345.32.ccls. 204/298.25.ccls.	US-PGPUB	}
		204/298.35.ccls.) and (156/345.24.ccls.		
		156/345.27.ccls. 204/298.03.ccls.	i	
		204/298.32.ccls.) and (control\$4 with		
		(substrate wafer workpiece) with temperature with during with (process\$3		
ļ		treatm\$3) with damag\$3)		
_	n	(118/719.ccls. 156/345.31.ccls.	USPAT;	2004/06/09 20:00
	ĭ	156/345.32.ccls. 204/298.25.ccls.	US-PGPUB	2004/00/09 20:00
		204/298.35.ccls.) and (156/345.24.ccls.	OU FGEOD	
		156/345.27.ccls. 204/298.03.ccls.		
]		204/298.32.ccls.) and (control\$4 with		
	ļ	(substrate wafer workpiece) with		
		temperature with damag\$3)	,	
			1	

_	79	(118/719.ccls. 156/345.31.ccls.	USPAT;	2004/06/09 20:00
		156/345.32.ccls. 204/298.25.ccls.	US-PGPUB	
		204/298.35.ccls.) and (156/345.24.ccls.		
		156/345.27.ccls. 204/298.03.ccls.		
		204/298.32.ccls.)		
_	24	· ·	USPAT;	2004/06/09 20:11
		156/345.32.ccls. 204/298.25.ccls.	US-PGPUB	2004/00/09 20:11
	1	204/298.35.ccls.) and (156/345.24.ccls.	05-19-06	
		156/345.27.ccls. 204/298.03.ccls.	•	
		204/298.32.ccls.) and (control\$4 with		
		temperature )		
_	0			
-	1	1 ()	USPAT;	2004/06/09 20:12
	İ	156/345.32.ccls. 204/298.25.ccls.	US-PGPUB	
		204/298.35.ccls.) and (156/345.24.ccls.		
		156/345.27.ccls. 204/298.03.ccls.		
		204/298.32.ccls.) and (control\$4 with		
	]	temperature with magnet\$ with propert\$3 }		
-	1	(118/719.ccls. 156/345.31.ccls.	USPAT;	2004/06/09 20:12
		156/345.32.ccls. 204/298.25.ccls.	US-PGPUB	
}		204/298.35.ccls.) and (control\$4 with		
		temperature with magnet\$ with propert\$3 )		
-	3	(156/345.24.ccls. 156/345.27.ccls.	USPAT;	2004/06/09 20:13
		204/298.03.ccls. 204/298.32.ccls.) and	US-PGPUB	
		(control\$4 with temperature with magnet\$		
		with propert\$3 )		
-	133	(control\$4 with temperature with magnet\$	EPO; JPO;	2004/06/09 20:13
		with propert\$3 )	DERWENT	2004/00/03 20:13
_	2	(control\$4 with temperature with magnet\$	EPO; JPO;	2004/06/09 20:14
	_	with propert\$3 with (during) with (treat\$4	DERWENT	2004/00/09 20:14
		process\$4))	DEKWENI	
<u>-</u>	11	(control\$4 with temperature with magnet\$	USPAT;	2004/06/00 00 00
		with propert\$3 with (during) with (treat\$4	US-PGPUB	2004/06/09 20:20
	1	process\$4))	US-PGPUB	1
_	65	(control\$4 with temperature with magnet\$	HCDAM.	2004/06/00 20 00
	"	with propert\$3 with (treat\$4 process\$4))	USPAT;	2004/06/09 20:20
l _	65	(control\$4 with temperature with magnet\$	US-PGPUB	0004/05/00 00 01
1	63	(concross4 with temperature with magnets	USPAT;	2004/06/09 20:21
l _	24	with propert\$3 with (treat\$4 process\$4))	US-PGPUB	1
1	24	(control\$4 with temperature with magnet\$	EPO; JPO;	2004/06/09 20:21
1_	788	with propert\$3 with (treat\$4 process\$4))	DERWENT	1
-	/88	(156/345.\$.ccls. 118/715/733.\$.ccls.) and	USPAT;	2004/06/10 11:27
-		((control\$4 with temperature) with	US-PGPUB	
	1.57	(substrate wafer workpiece))		1
-	177	(156/345.\$.ccls. 118/715/733.\$.ccls.) and	USPAT;	2004/06/10 11:27
		((control\$4 with temperature) with	US-PGPUB	
		(substrate wafer workpiece) with (during))		
_	13	(156/345.\$.ccls. 118/715/733.\$.ccls.) and	USPAT;	2004/06/10 13:13
		((control\$4 adj temperature) adj	US-PGPUB	
		(substrate wafer workpiece) adj (during))		1
-	22	(156/345.\$.ccls.) and ((low adj	USPAT;	2004/06/10 13:14
		temperature) adj (etch\$3))	US-PGPUB	
-	10	("5571366"   "5572366"   "5645683"	USPAT	2004/06/10 13:17
	ł	"5695564"   "5695654"   "5700734"		
		"5756401"   "6008139"   "6046116"		ł l
		"6087264").PN.		
-	18	(156/345.\$.ccls. 216/\$.ccls.) and (plasma	USPAT;	2004/06/10 15:53
		same (low adj ion adj energy) same (high	US-PGPUB	\\ \_\5004\09\10 T2:23 \\
		adj density))	OU EGEUD	
			<u> </u>	